
High-resolution depth profiling: Overview

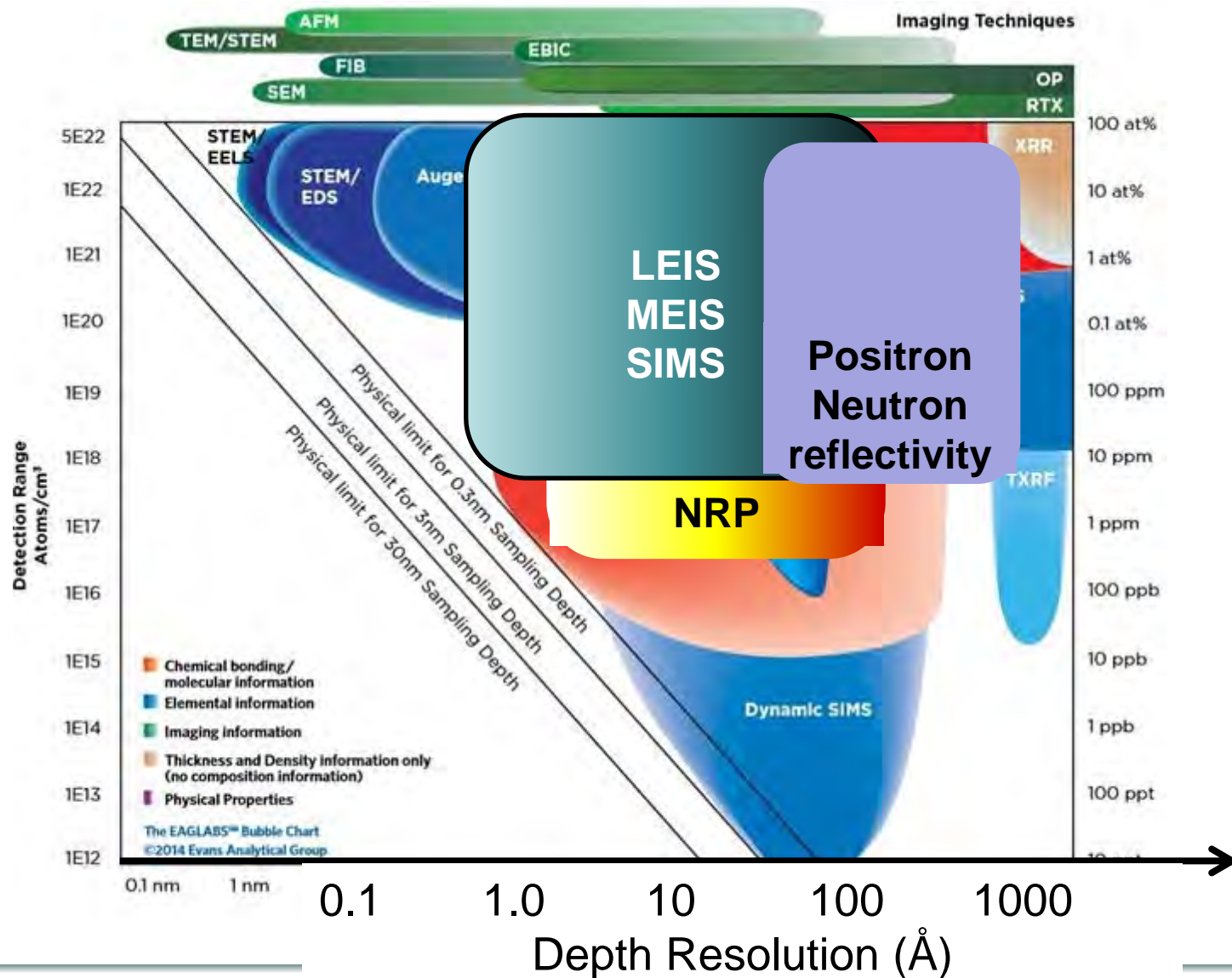
Lyudmila V. Goncharova

*Department of Physics and Astronomy,
University of Western Ontario,
London, Ontario, Canada*

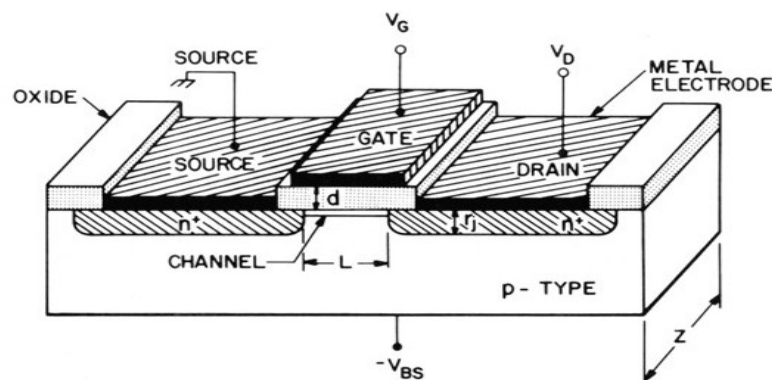


University of Western Ontario, August 12, 2016

Analytical resolution vs detection limit

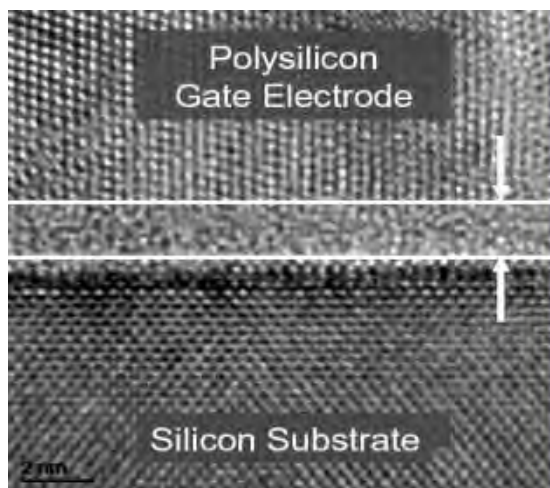


Physical Limits of SiO₂ Gate Dielectrics

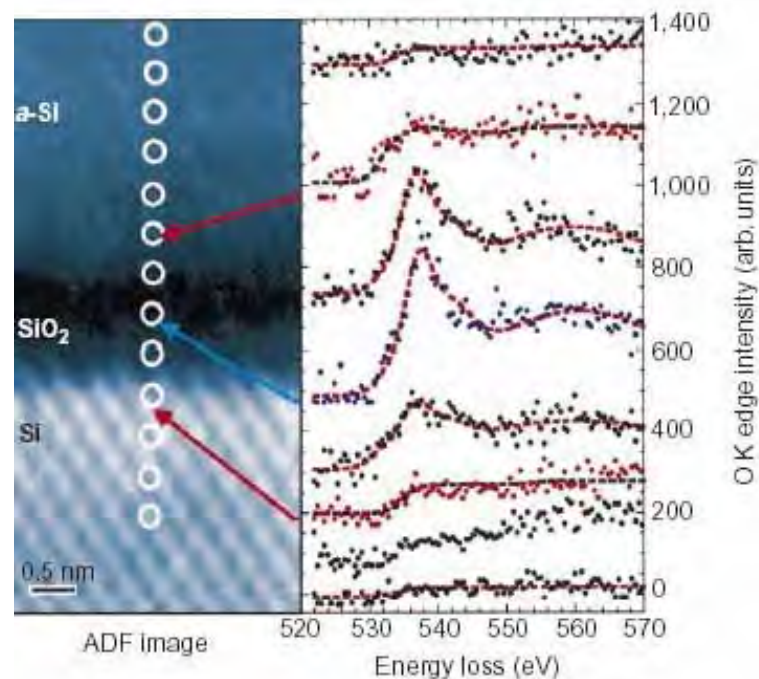


Schematic diagram of MOSFET*

(* from Sze S.M. *Physics of Semiconductor Devices*)

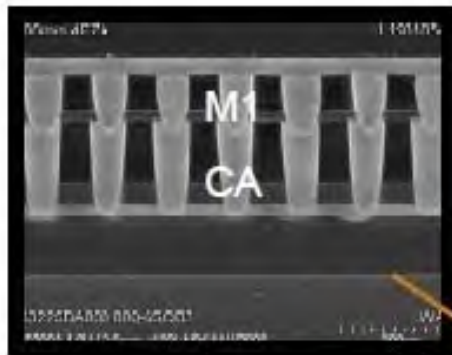


Scanning electron micrograph of cross-sectioned NMOS transistor



- EELS O-K edge spectra recorded point by point across a gate stack containing a thin gate oxide
D. A. Muller et. al., Nature, 399, 758-761 (1999)
- Bulk SiO₂ properties (e.g. large bandgap) lost for films ≤ 8 Å in thickness

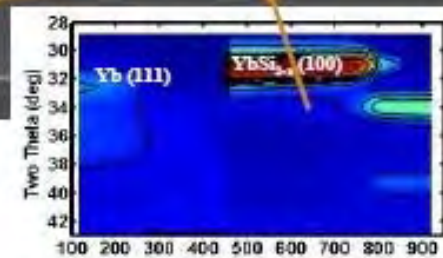
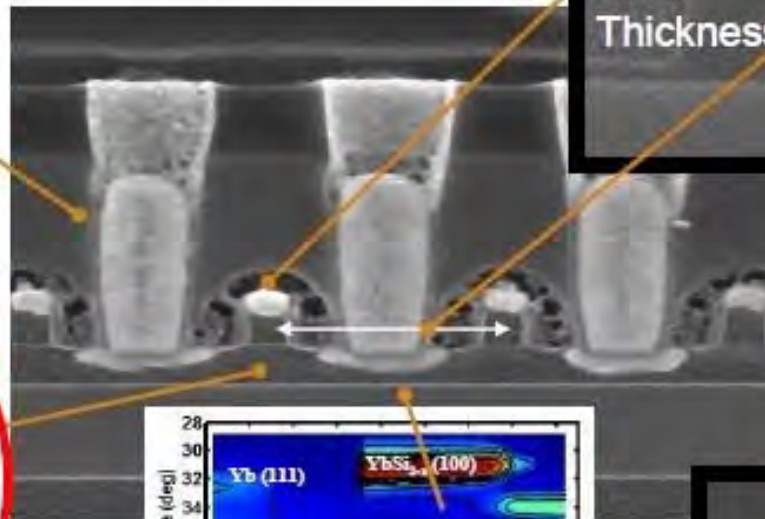
Making things smaller – still the Si way!



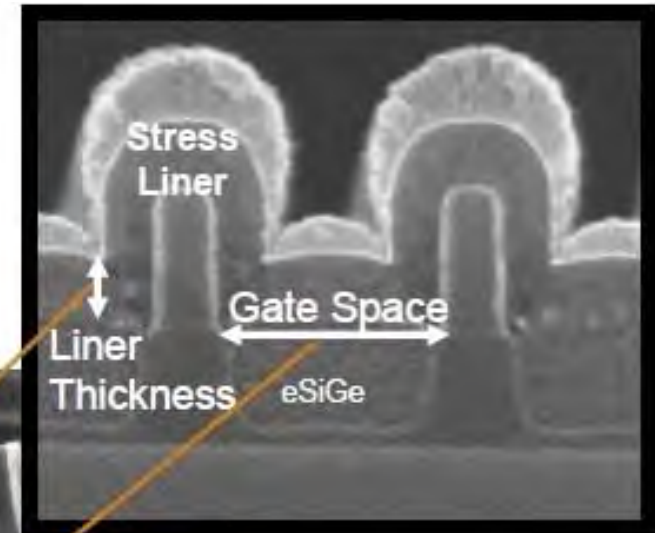
Contacts



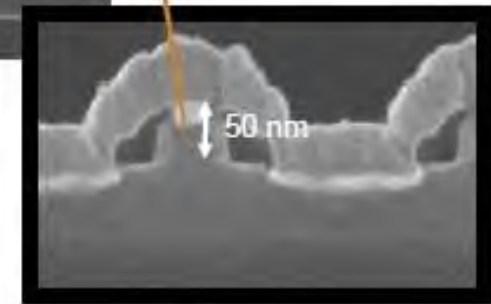
*Dielectric scaling:
Metal gate/high κ*



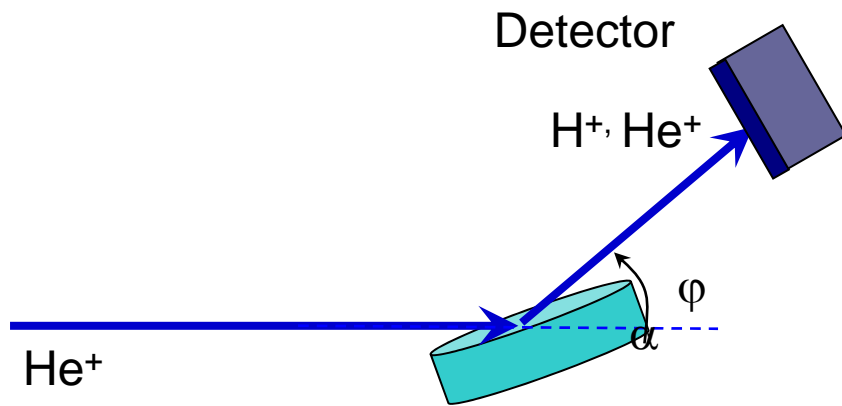
Dual Silicide



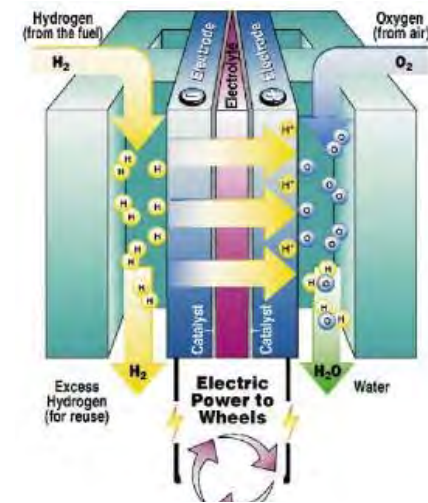
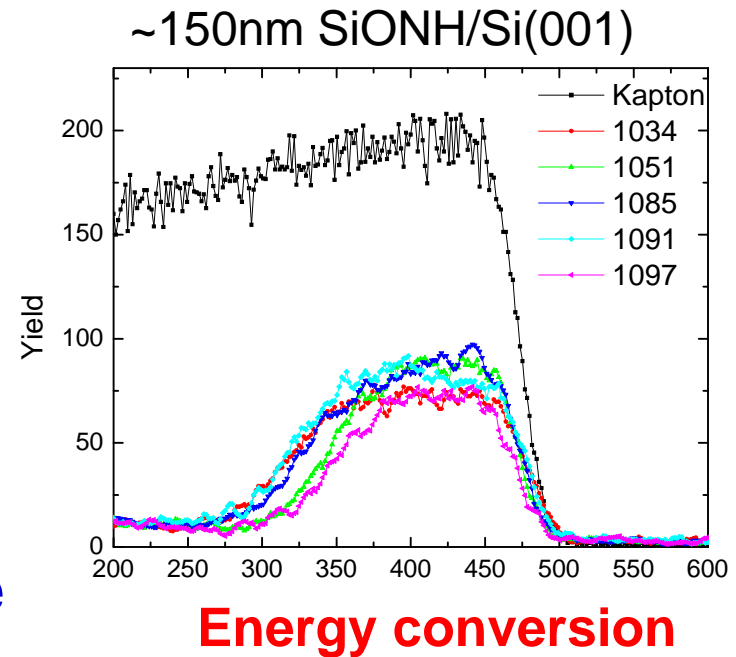
Gate Height



Missing element from the picture... hydrogen!

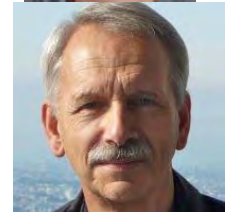


- Novel materials
➡ Hydrogen storage
- Fuel cells, functional membranes
➡ Energy conversion
- Nanoscale catalysis and corrosion
➡ Hydrogen diffusion

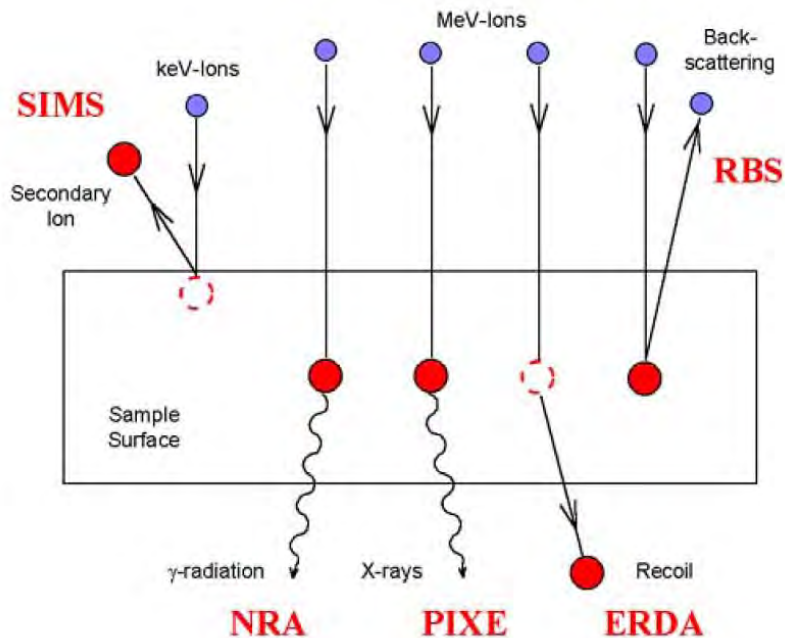


Methods and presenters today...

- 9:00am **Nuclear reaction analysis and narrow profiling**, *Fernanda Stedile, Universidade Federal do Rio Grande do Sul*
- 10:20am **Medium energy ion scattering**, *Jaap van den Berg, University of Huddersfield*
- 11:20am **Secondary ion mass spectrometry applications in materials characterization**, *Stamen Dimov, Surface Science Western*
- 13:20pm **Positron annihilation for defect engineering and analysis for electronic materials**, *Peter Simpson, Western and Andy Knights, McMaster*
- 14:20am **Neutron scattering and reflectivity for depth-profiled information**, *Jamie Noël, Western University*



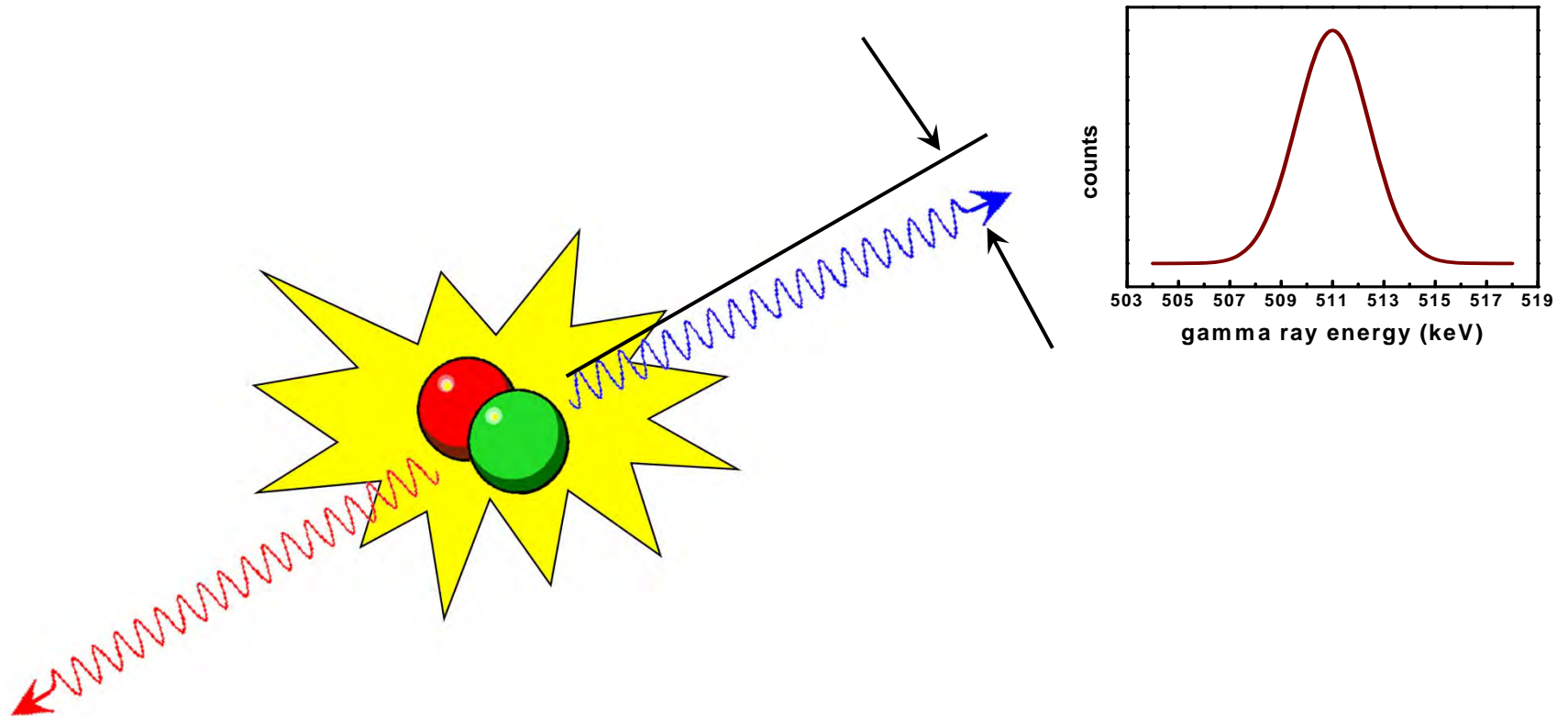
Ion-solid interactions



- (1) elastic scattering (**RBS, LEIS, MEIS**)
- (2) fast recoils arising from elastic scattering
- (3) steering effects due to the crystalline structure of target atoms
- (4) inelastic processes: energy loss as a function of depth
- (5) nuclear reactions (**NRA and NRP**)
- (6) interference of elastic scattering and nuclear interaction amplitudes, which leads to so-called resonant scattering

Positron Annihilation

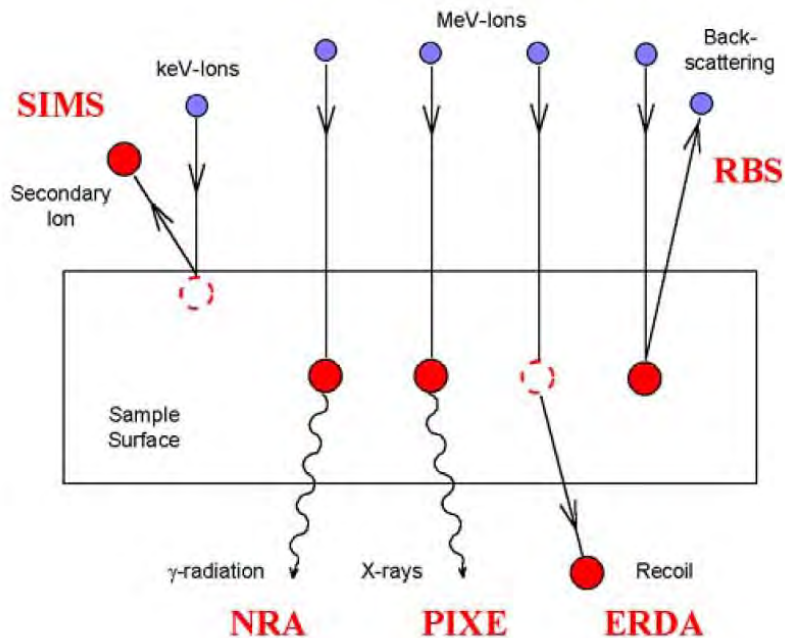
- Vacancies present in any material...



Neutrons and Neutron Reflectometry

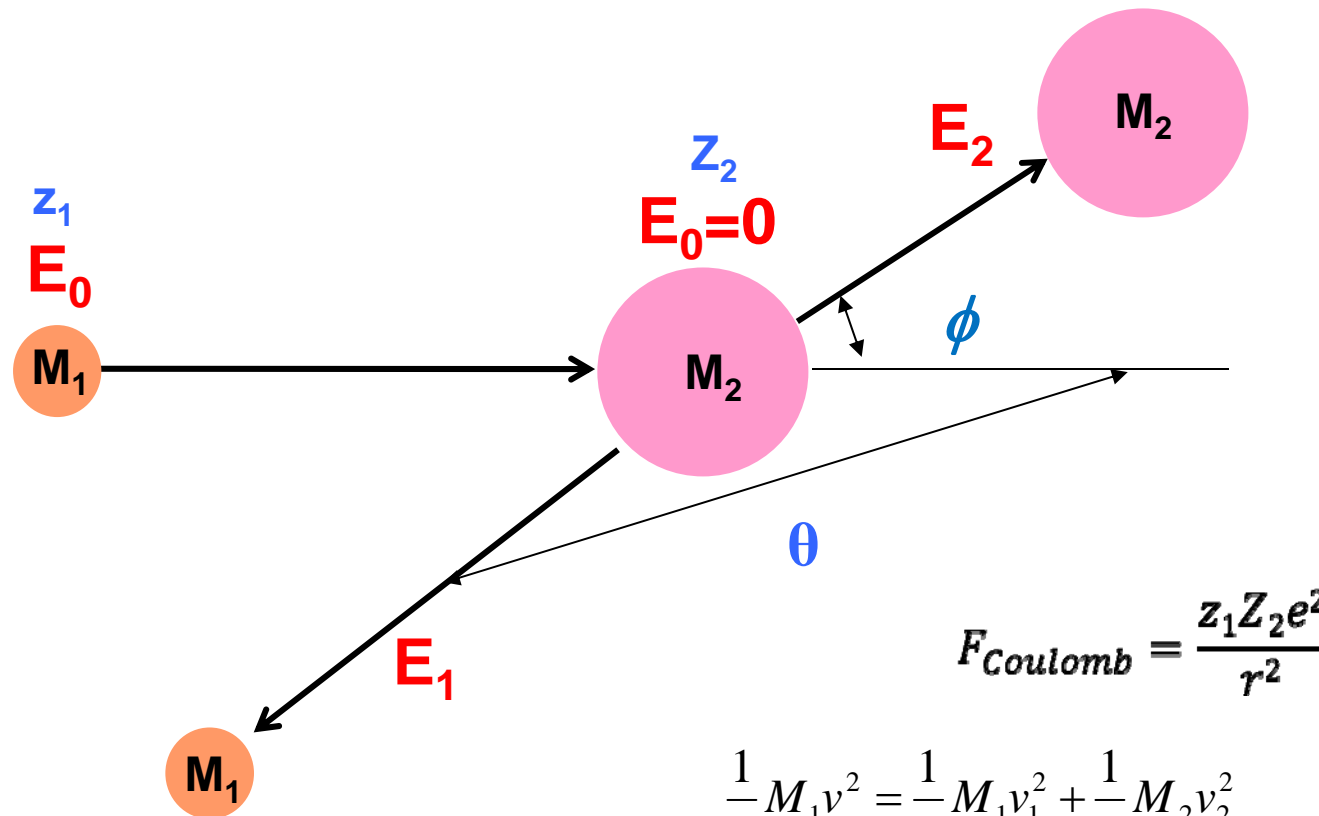
- Interact with atomic nuclei via strong nuclear force
- Thermal neutron energy $\sim 27 \text{ meV}$ ($k_B T$)
 - Velocity $\sim 2200 \text{ m/s}$
 - Wavelength $\sim \text{few } \text{\AA}$
- Interaction strength and direction (attractive or repulsive) are independent of atomic number
 - Different with isotope
 - Coherent bound neutron scattering length

Ion-solid interactions



- (1) elastic scattering (**RBS, LEIS, MEIS**)
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Elastic Collisions



$$\frac{1}{2} M_1 v^2 = \frac{1}{2} M_1 v_1^2 + \frac{1}{2} M_2 v_2^2 \quad (\text{Eq.1})$$

$$M_1 v = M_1 v_1 \cos \theta + M_2 v_2 \cos \phi \quad (\text{Eq.2})$$

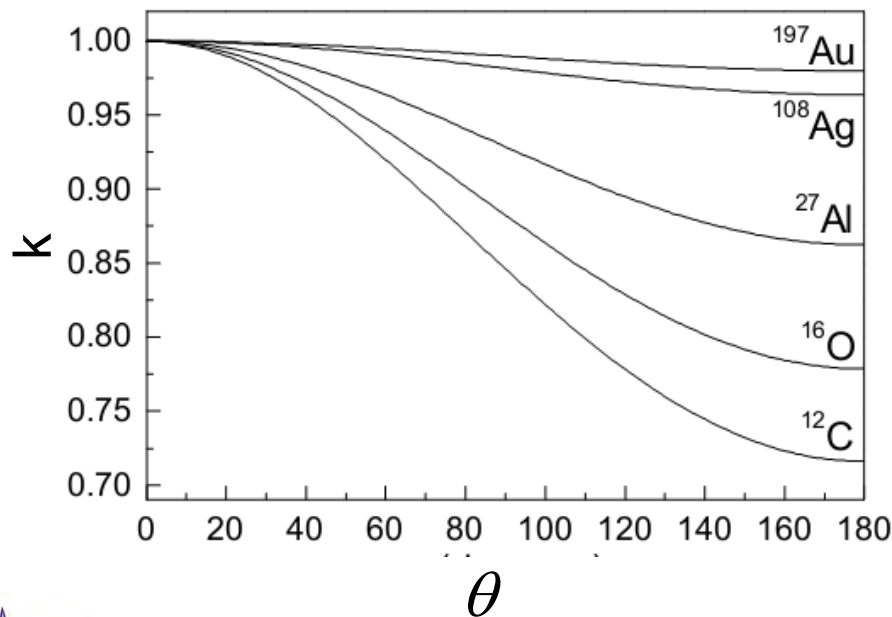
$$0 = M_1 v_1 \sin \theta - M_2 v_2 \sin \phi \quad (\text{Eq.3})$$

Kinematic Factor, k

From Eq. 2 and 3, eliminating ϕ first, then v_2 , one finds the ratio of particle velocities, and we can show that the energy of projectile (M_1) after collision can be found by the following relationship:

$$E_1 = E_0 \left[\frac{(M_2^2 - M_1^2 \sin^2 \theta)^{1/2} + M_1 \cos \theta}{M_2 + M_1} \right]^2$$

Ratio of E_1 and E_0 is called **kinematic factor**: $k = \frac{E_1}{E_0} = \left[\frac{(M_2^2 - M_1^2 \sin^2 \theta)^{1/2} + M_1 \cos \theta}{M_2 + M_1} \right]^2$



Plot of the kinematic factor, k, vs scattering angle for H^+ scattering from various targets

Advantages of Ion Beams

- Can be used for material modification and analysis

- Mass Specific
- Kinematic factor
$$E_1 = E_o \left(\frac{\sqrt{M_2^2 - M_1^2 \sin^2 \theta} + M_1 \cos \theta}{M_1 + M_2} \right)^2$$

- Cross sections are very well known

- Good depth resolution

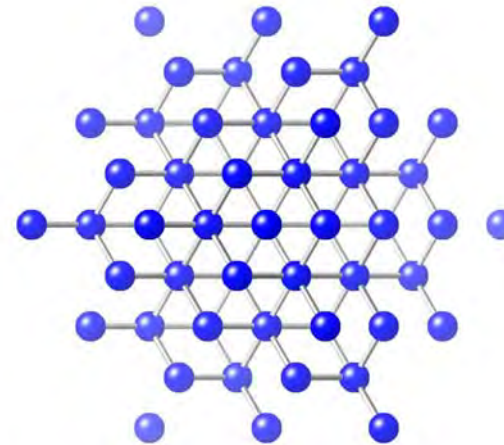
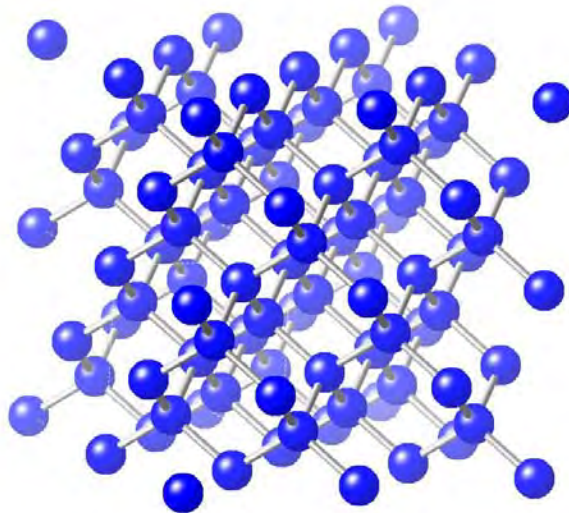
- Penetrating (can access buried interfaces)

- What about substrate?
 - can use channeling and blocking effects

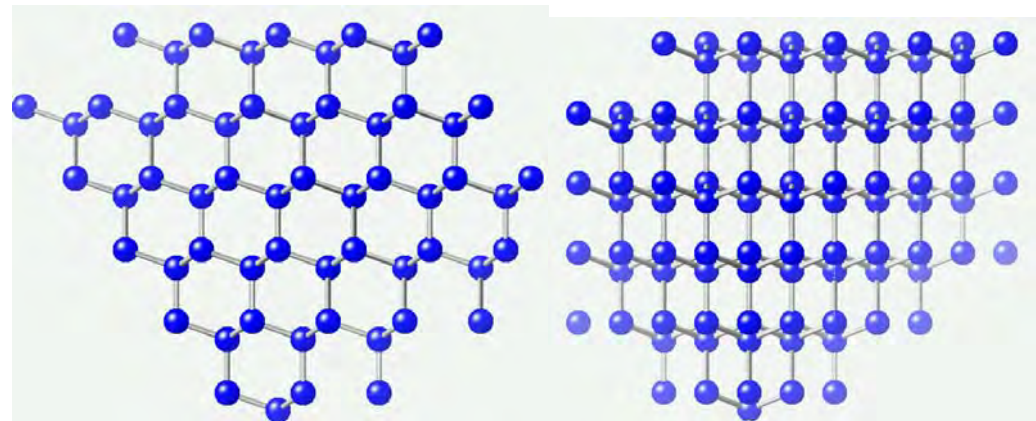


Ion channeling and blocking

Si (diamond structure)

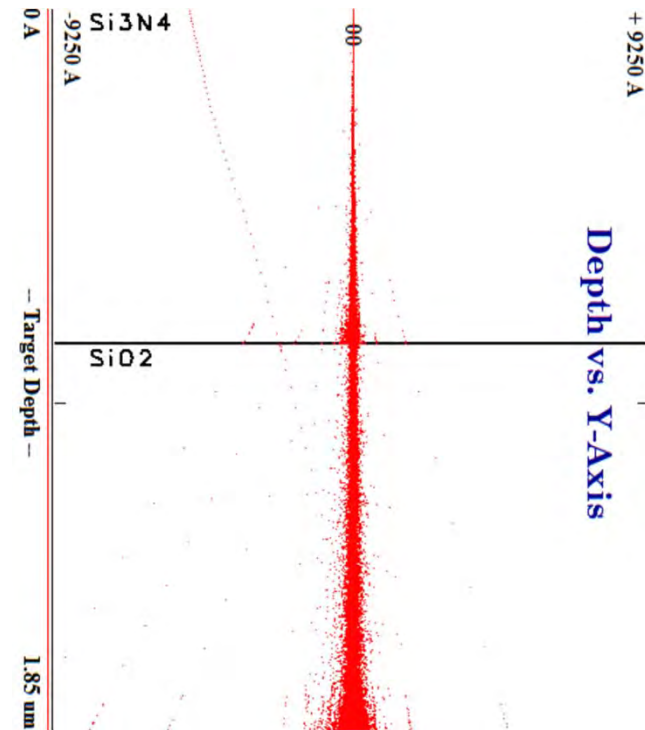
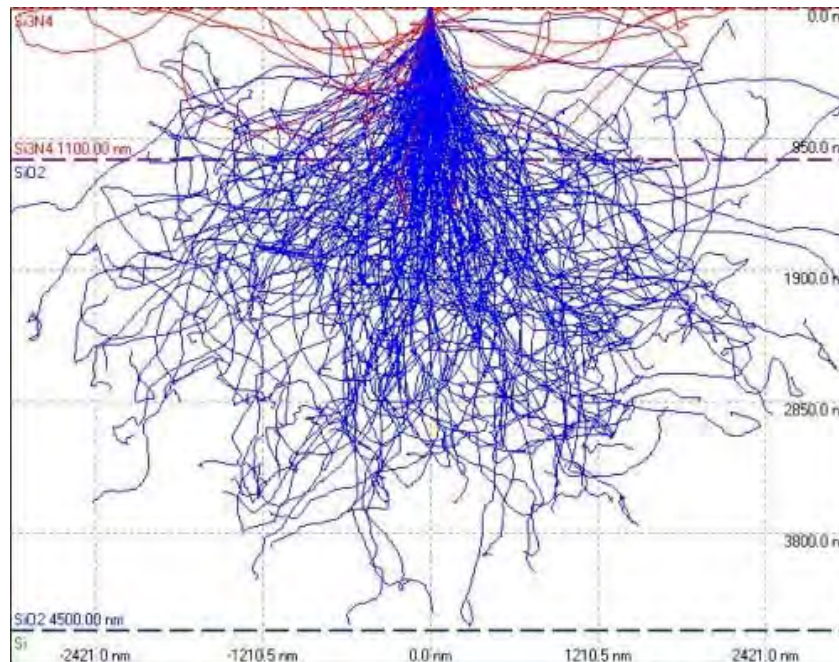


- Si(111) – side view



Electrons vs Ions

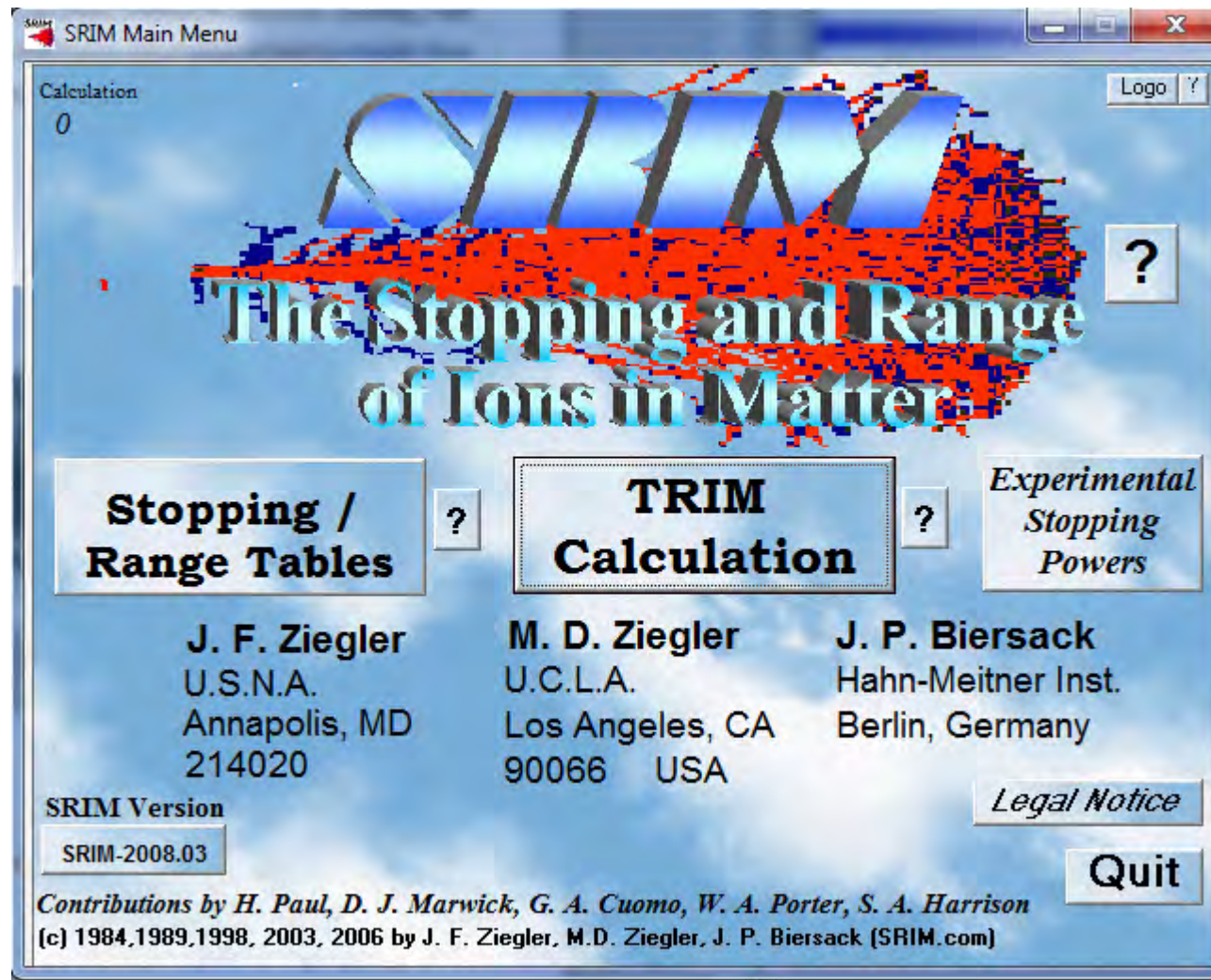
When an ion collides with electron clouds in the solid, it does not lose much energy and its direction of motion is hardly change, in a contrast with electrons colliding with electrons



18keV e⁻ and 18 keV He⁺ striking a Si₃N₄ layer with a SiO₂ substrate

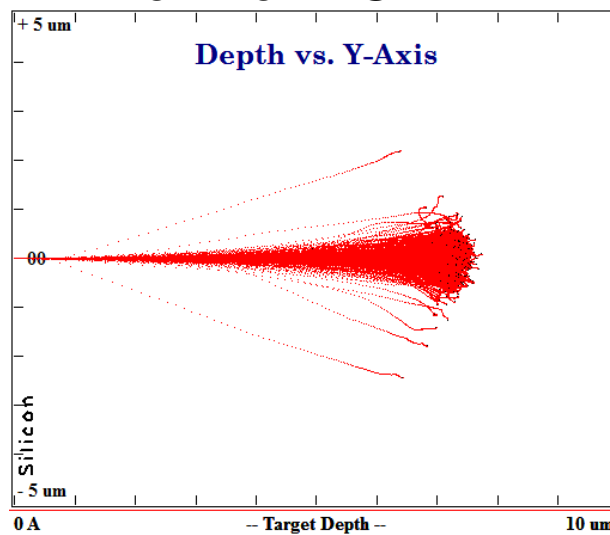
SRIM

<http://www.srim.org/> ⇒ [Download SRIM-2013](#)

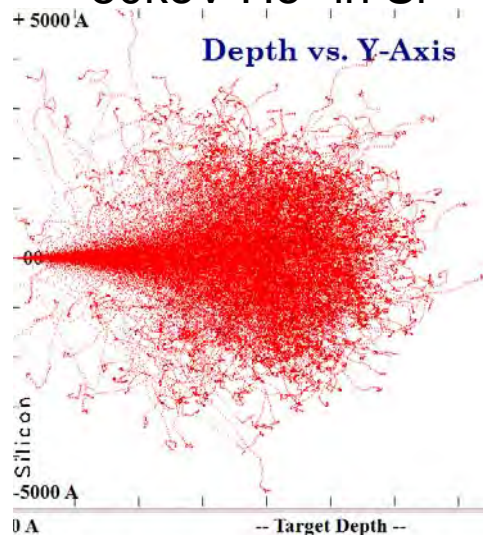


Calculated Ion Trajectories

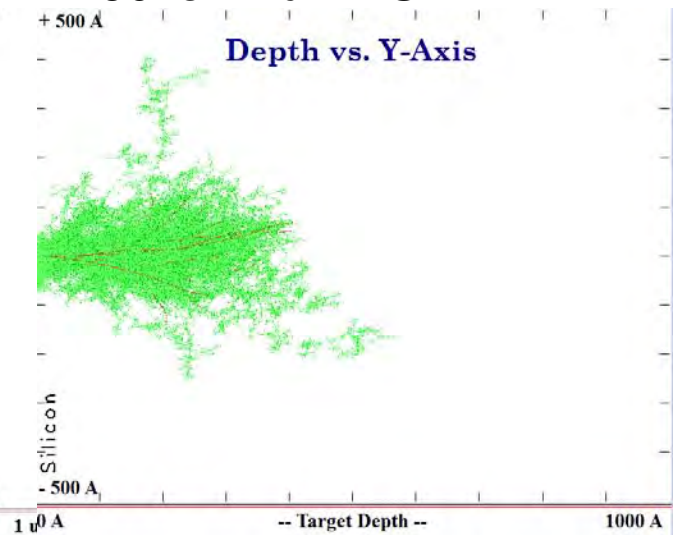
2MeV He⁺ in Si



50keV He⁺ in Si

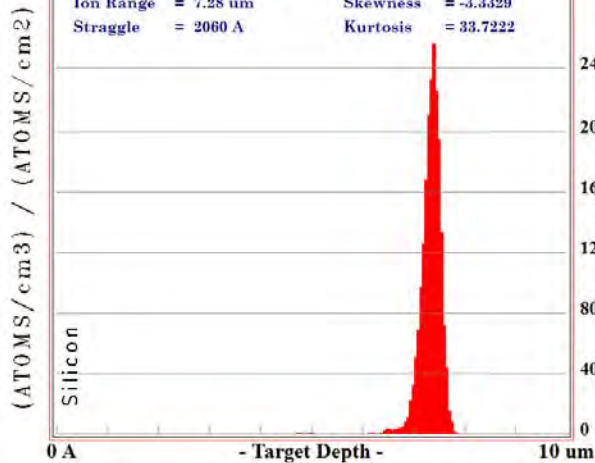


50keV Au⁺ in Si



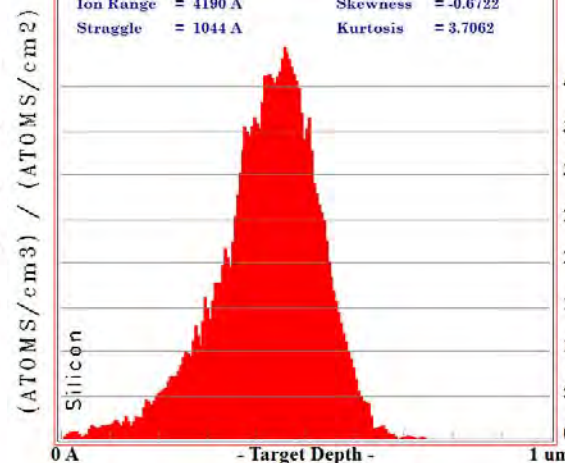
ION RANGES

Ion Range = 7.28 um
Straggle = 2060 A
Skewness = -3.3329
Kurtosis = 33.7222



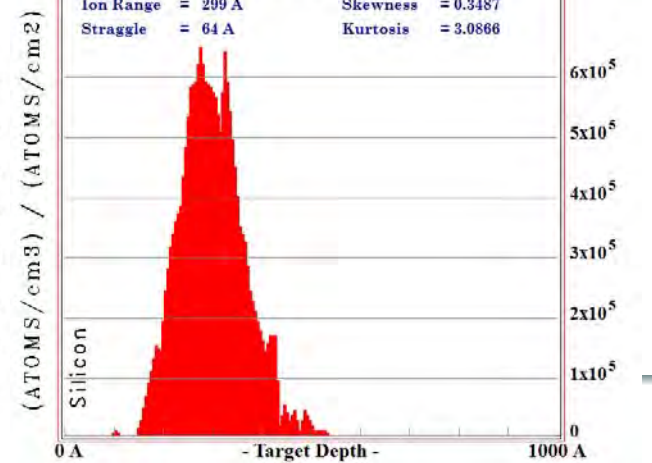
ION RANGES

Ion Range = 4190 A
Straggle = 1044 A
Skewness = -0.6722
Kurtosis = 3.7062

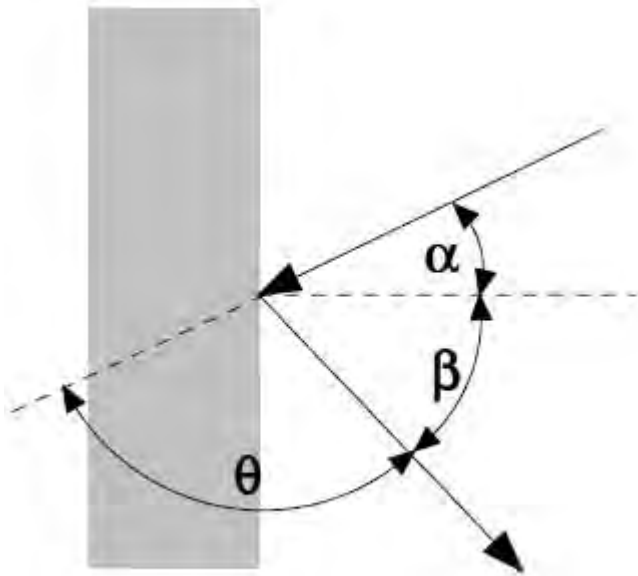


ION RANGES

Ion Range = 299 A
Straggle = 64 A
Skewness = 0.3487
Kurtosis = 3.0866



Rutherford Backscattering: geometry and kinematics



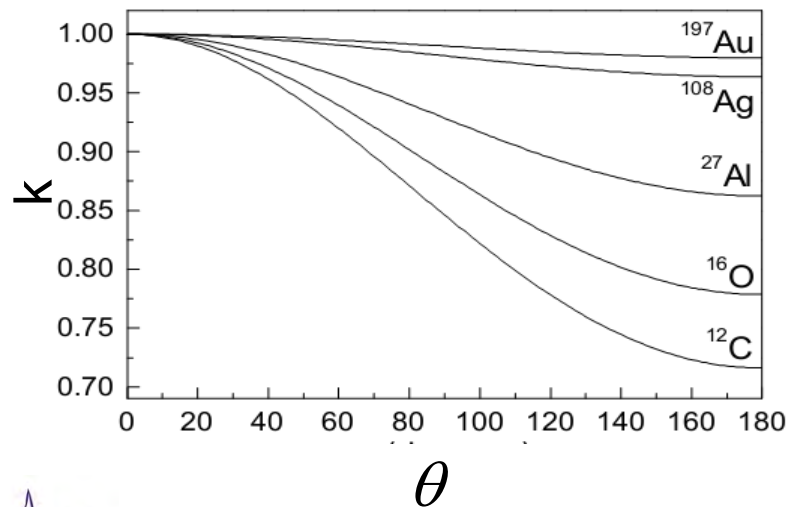
$$E_1 = k E_o$$

$$k = \frac{E_1}{E_o} = \left[\frac{(M_2^2 - M_1^2 \sin^2 \theta)^{1/2} + M_1 \cos \theta}{M_2 + M_1} \right]^2$$

α : incident angle

β : exit angle

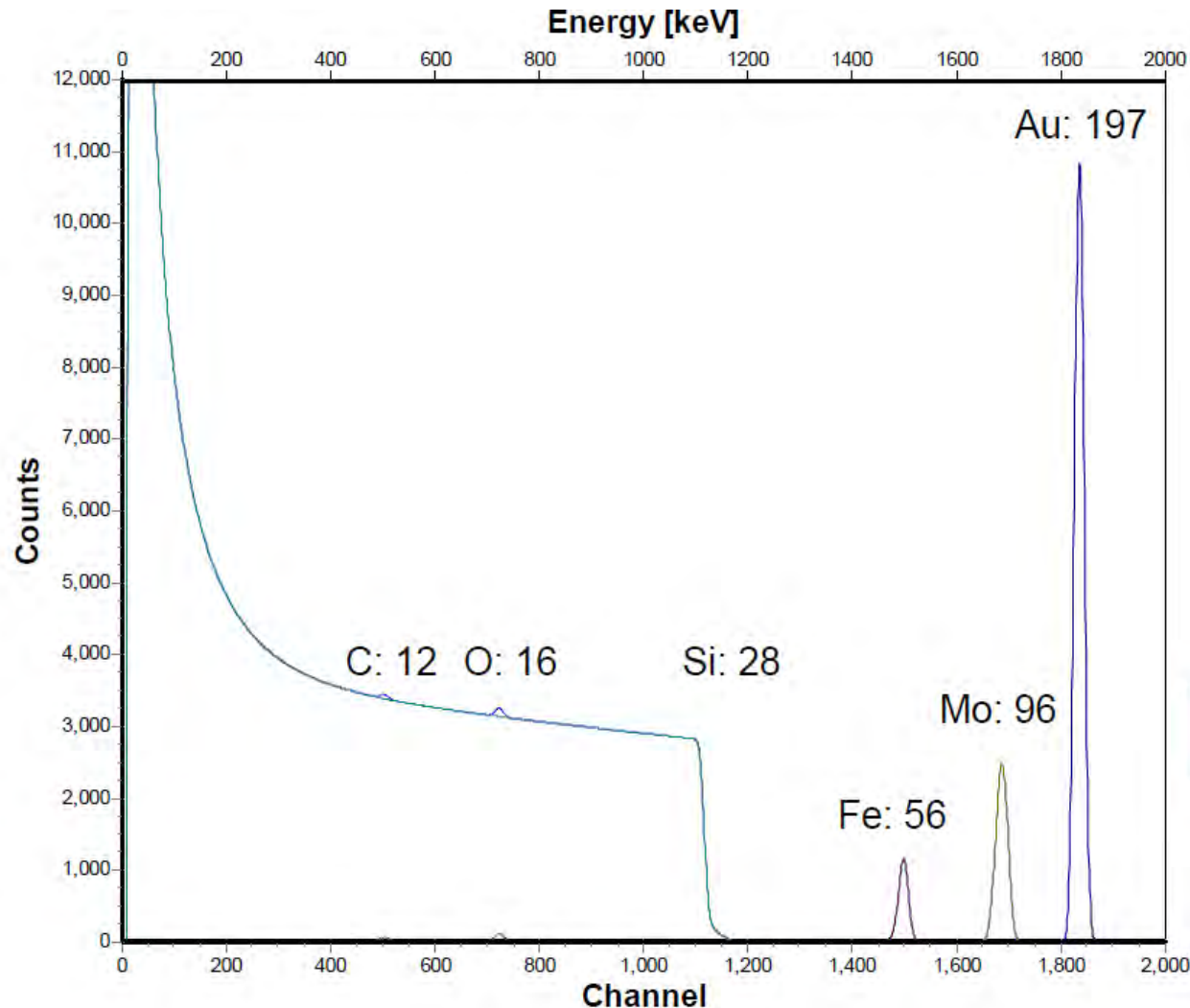
θ : scattering angle



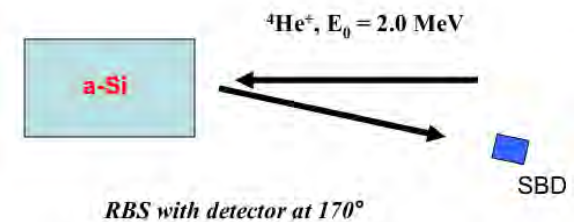
Optimized mass resolution for:

$$160^\circ < \theta < 170^\circ$$

RBS Scattering kinematics: example 1



2 MeV $^4\text{He}^+$, $\theta = 165^\circ$
Backscattered from
C, O, Fe, Mo, Au
 3×10^{16} atoms/cm²
each
on Si substrate



Key features of RBS

Ability to quantify depth profile of buried species with a precision of $\sim 3\%$

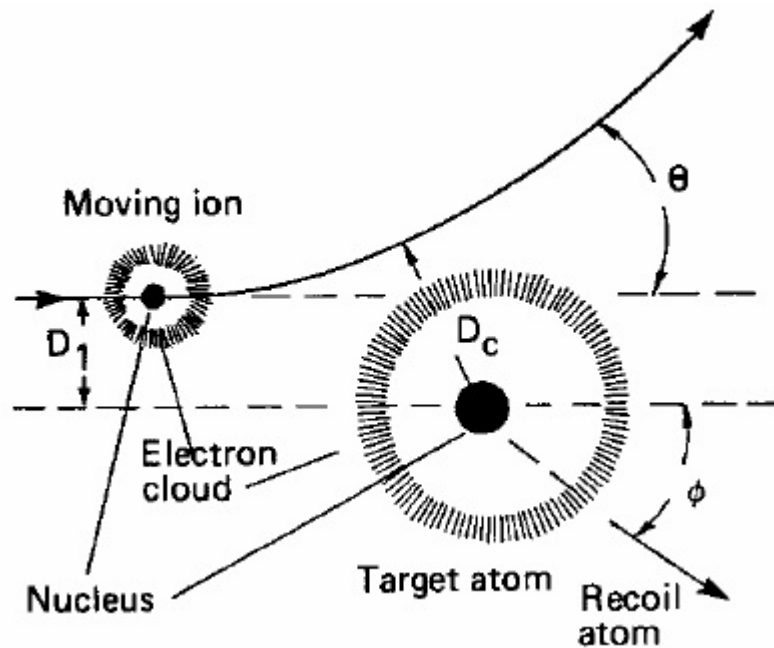
Qualitative information: **kinematic factor**, k

$$k = \frac{E_1}{E_o} = \left[\frac{(M_2^2 - M_1^2 \sin^2 \theta)^{1/2} + M_1 \cos \theta}{M_2 + M_1} \right]^2$$

Quantitative: **scattering cross section**, σ

$$\frac{d\sigma}{d\Omega} \equiv \sigma(\theta) = \left(\frac{Z_1 Z_2 e^2}{4 E \sin^2 \left(\frac{\theta}{2} \right)} \right)^2$$

Rutherford Cross Section



- Neglecting shielding by electron clouds
- Distance of closest approach large enough that nuclear force is negligible
- ⇒ Rutherford scattering cross section

$$\frac{d\sigma}{d\Omega} \equiv \sigma(\theta) = \left(\frac{Z_1 Z_2 e^2}{4E \sin^2\left(\frac{\theta}{2}\right)} \right)^2$$

Note that sensitivity increases with:

- Increasing Z_1
- Increasing Z_2
- Decreasing E

RBS spectra from thin and thick films

The integrated peak count A_i for each element on the surface can be calculated using this equation:

$$A_i = (Nt)_i \times Q \times \Omega \times \frac{\sigma(E, \theta)}{\cos \theta}$$

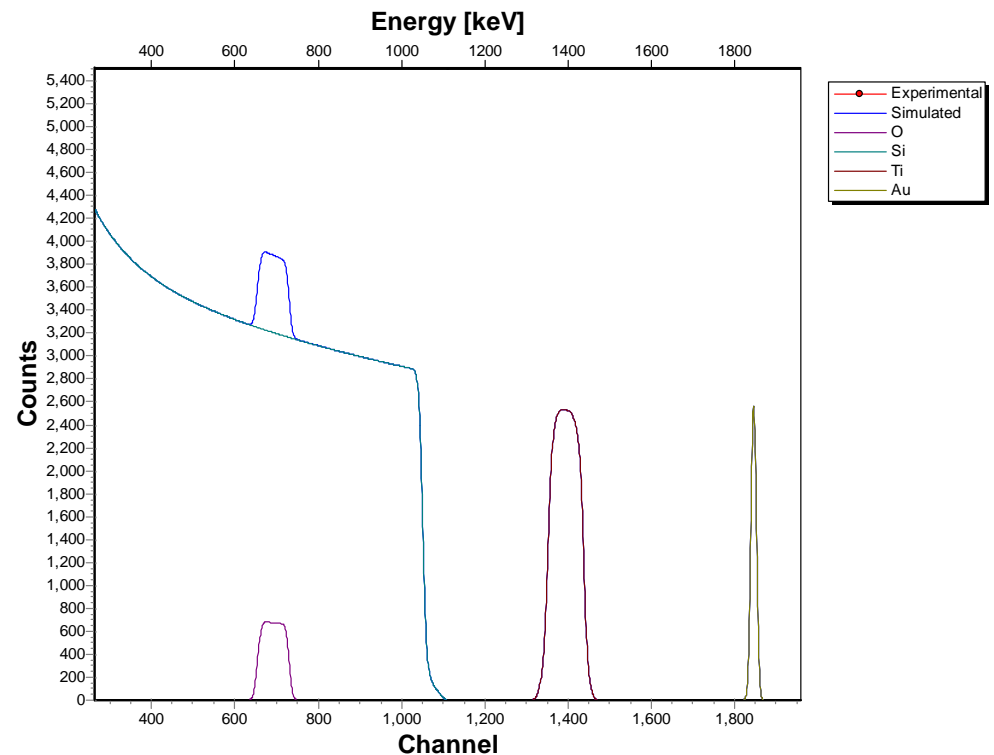
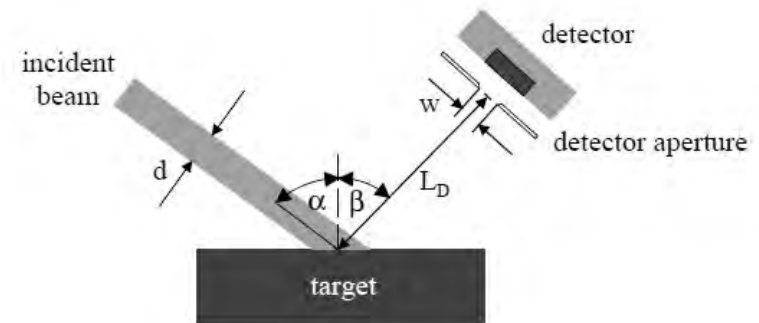
where

$(Nt)_i$ is areal density, atoms per unit area;

Q – ion beam fluency;

Ω – solid angle of the detector;

$\sigma(E, \theta)/\cos \theta$ – cross section of an element

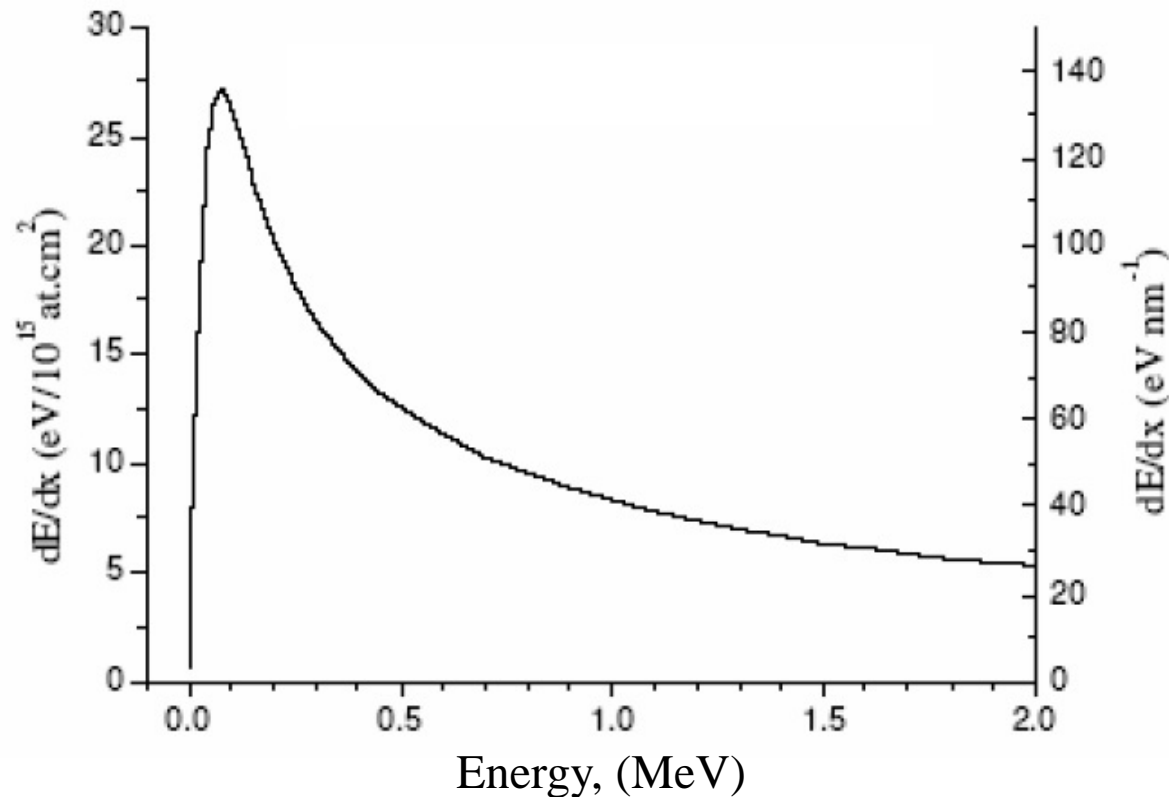


Ion dose (fluency), solid angle, cross section

- **Ion dose (fluency), the number of incident particles (collected charge)**
 - measured by Faraday cup
 - $Q = I \times t$
- **Solid angle, in steradians, sr**
 - stays constant for a particular detector/detector slit
 - need to be verified by the calibration standard measurements
- **Cross section (or differential cross section), in cm²/sr of the element**
 - well known (tabulated) in Rutherford cross section regime

High-resolution depth profiling parameters

- Energy dependence of dE/dx for H^+ and He^+
 - Maximum of $\sim 14 \text{ eV/\AA}$ at $\sim 100 \text{ keV}$ for Si
- ⇒ This helps! Plus use of better ion detection equipment!

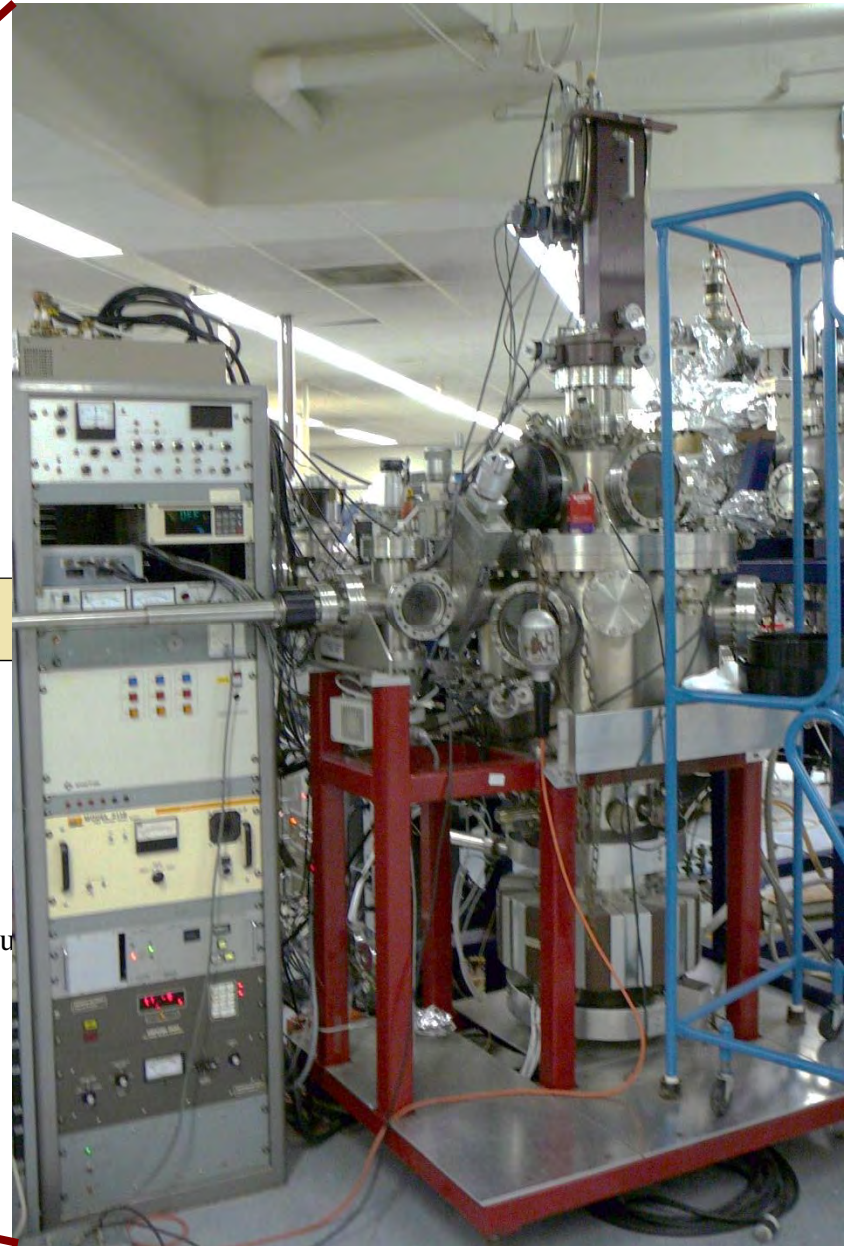
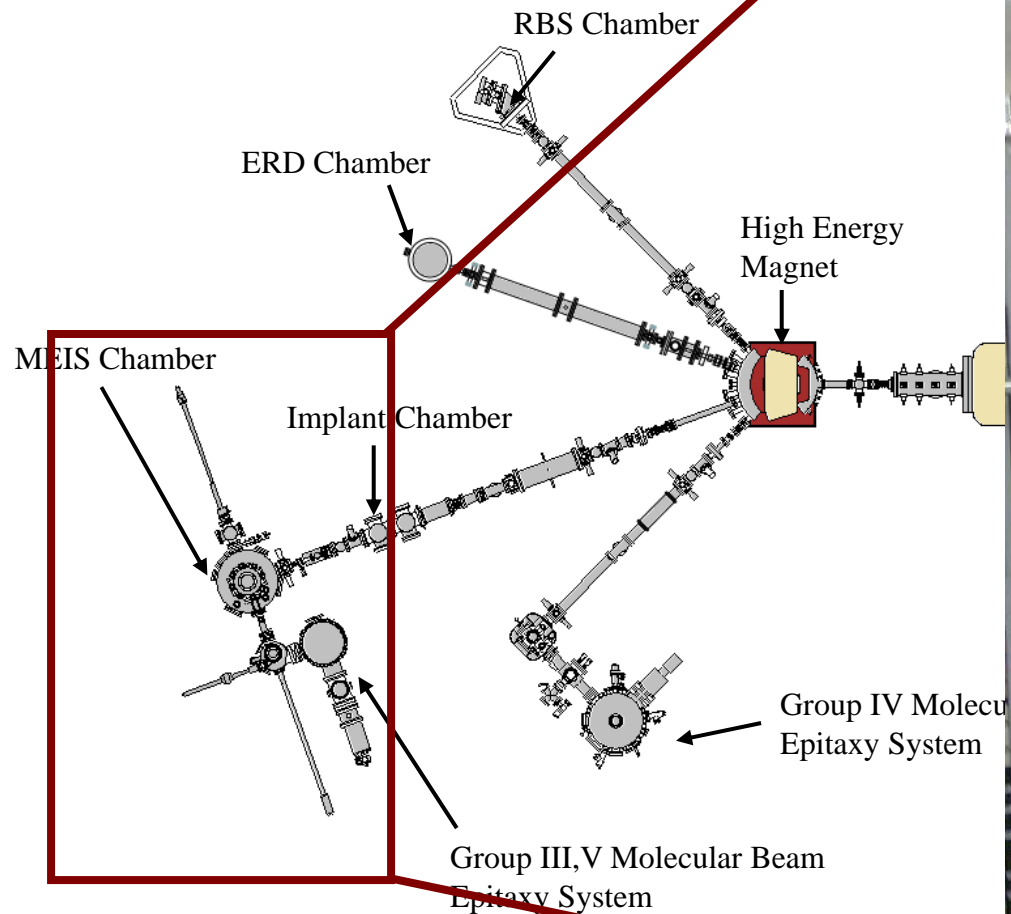


Ion detection equipment

- Detector energy resolution $< 1\text{keV}$
- Magnetic spectrometers
 - Kyoto University (Kimura)
 - Kobelco
- Electrostatic analyzers
 - FOM – IBM (Tromp, van der Veen)
 - High Voltage Engineering
 - Ion-TOF
- TOF detectors



MEIS at Western University



Development of 3D-MEIS



RIKEN S. Shimoda and T. Kobayashi

3D-MEIS

- Pulsed ion beam
- Scattered (and/or recoiled) particles are detected

- 2D blocking pattern
- flight times of scattered (and/or recoiled) particles

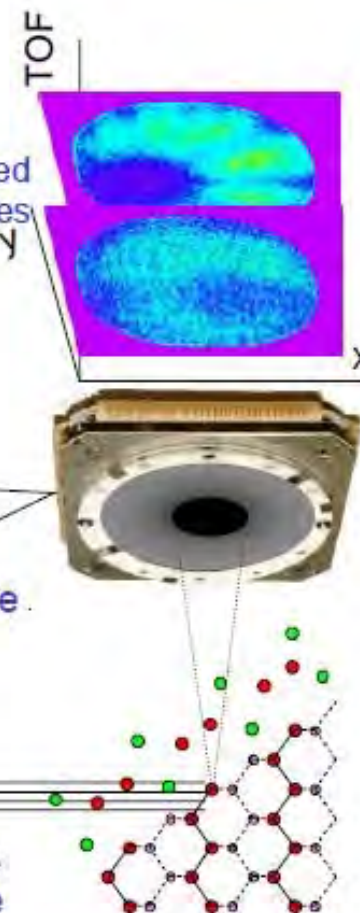
3D detector
position-sensitive and time-resolving
MCP detector

wide solid angle

incident beam

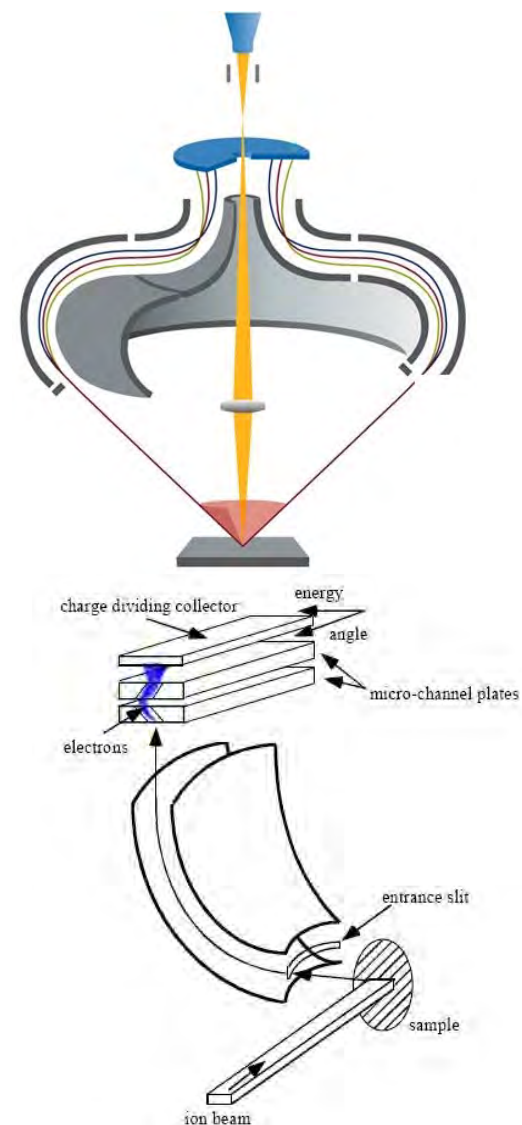
- Ion : He⁺
- Energy : 100 keV
- Repetition : 500 kHz

sample
periodic atomic structure



Uncertainties in depth profiling analysis

Issues.	What they affect	Solution
Neutralization ratio for H⁺ (He⁺, etc.)	Absolute concentrations (relative – ok)	<ul style="list-style-type: none"> • Measurement by SSD • Reference samples
Energy loss and straggling parameters for H⁺ in materials	Scaling of the depth; modeling	<ul style="list-style-type: none"> • Independent analysis by TEM, XPS • Reference
Non-gaussian energy distribution and non-statistical number of loss events	Peak shape; modeling, especially at the surface	<ul style="list-style-type: none"> • Not an issue for films >2nm; new basic theory needed
Film thickness, roughness and compositional gradient	May be confused with each other	<ul style="list-style-type: none"> • Independent measurements by TEM, AFM, XPS, etc.



Electrostatic detectors

$$A_i = (Nt)_i \times Q \times \Omega \times \frac{\sigma(E, \theta)}{\cos \theta} \times f^+$$

Need to detect hydrogen with high sensitivity and high depth resolution...

Some advantages of ERDA: good dynamic range; excellent hydrogen sensitivity; very well suited for analysis of light elements

Some disadvantages: Resolution; Sensitivity to surface contaminations

Method	High Sensitivity	High Resolution	Quantitative
SIMS	+	±	—
ERDA	+	-	+
NRA/NRP	+	±	+
LEIS	+	±	±
ME-ERD	+	+	±

Common Pitfalls for ion detection

- **Damage effects are significant \Rightarrow surface needs to be refreshed under the beam**
- **Uniform lateral distribution is assumed**
- **Charge fractions can vary between samples**
- **Accurate background fit is necessary to get quantitative fitting \Rightarrow calculations are necessary!**